

## Silicon PNP Power Transistors

## 2SB536

## DESCRIPTION

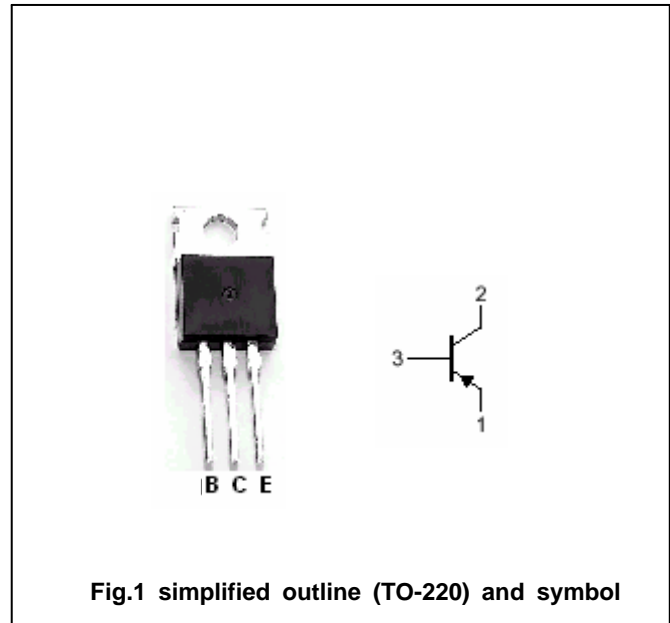
- With TO-220C package
- Complement to type 2SD381
- Low collector saturation voltage

## APPLICATIONS

- Audio frequency power amplifier
- Low speed power switching

## PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base

Absolute maximum ratings( $T_a=25$  )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-130	V
$V_{CEO}$	Collector-emitter voltage	Open base	-120	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-1.5	A
$I_{CM}$	Collector current-peak		-3.0	A
$I_B$	Base current		-0.3	A
$P_T$	Total power dissipation	$T_a=25$	1.5	W
		$T_C=25$	20	
$T_j$	Junction temperature		150	
$T_{stg}$	Storage temperature		-50~150	

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA; I <sub>B</sub> =0	-120			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-1A; I <sub>B</sub> =-0.1A			-2.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =-1A; I <sub>B</sub> =-0.1A			-1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-120V; I <sub>E</sub> =0			-1.0	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =-3V; I <sub>C</sub> =0			-1.0	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =-5mA; V <sub>CE</sub> =-5V	25			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =-0.3A; V <sub>CE</sub> =-5V	40		250	
C <sub>OB</sub>	Output capacitance	I <sub>E</sub> =0; V <sub>CB</sub> =-10V; f=1MHz		35		pF
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =-0.1A; V <sub>CE</sub> =-5V		40		MHz

◆ h<sub>FE-2</sub> Classifications

N	M	L	K
40-80	60-120	80-160	120-250

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PACKAGE OUTLINE



Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.10$ mm)